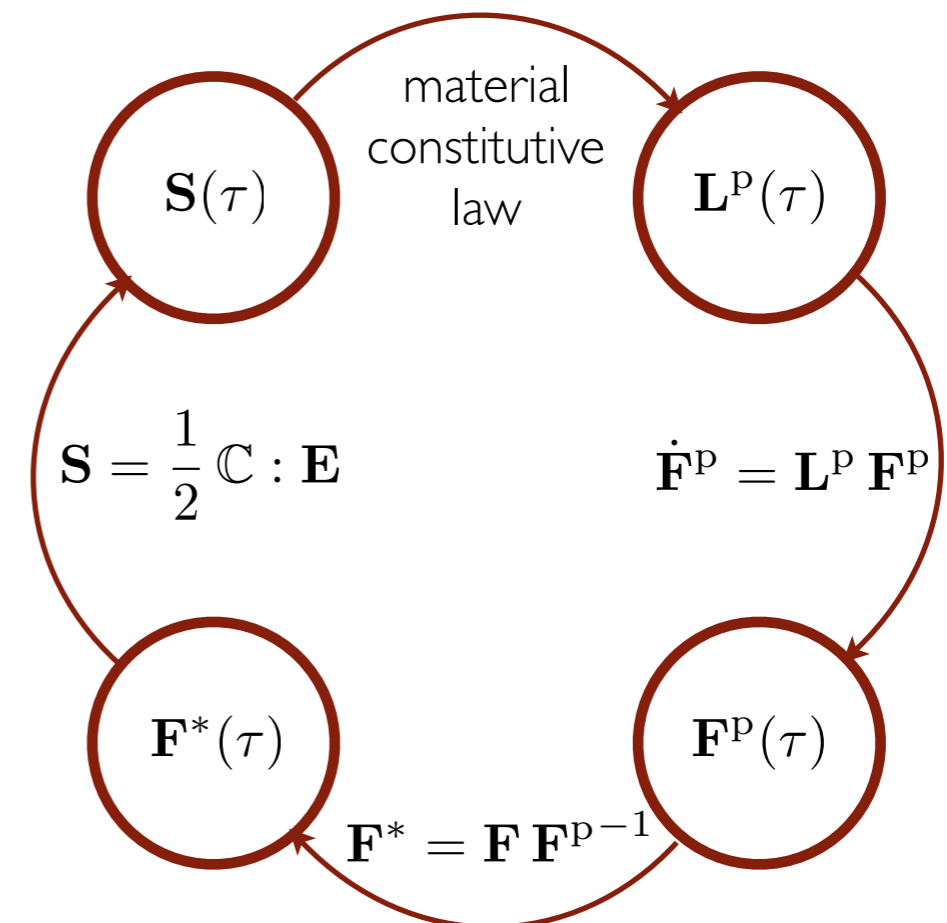
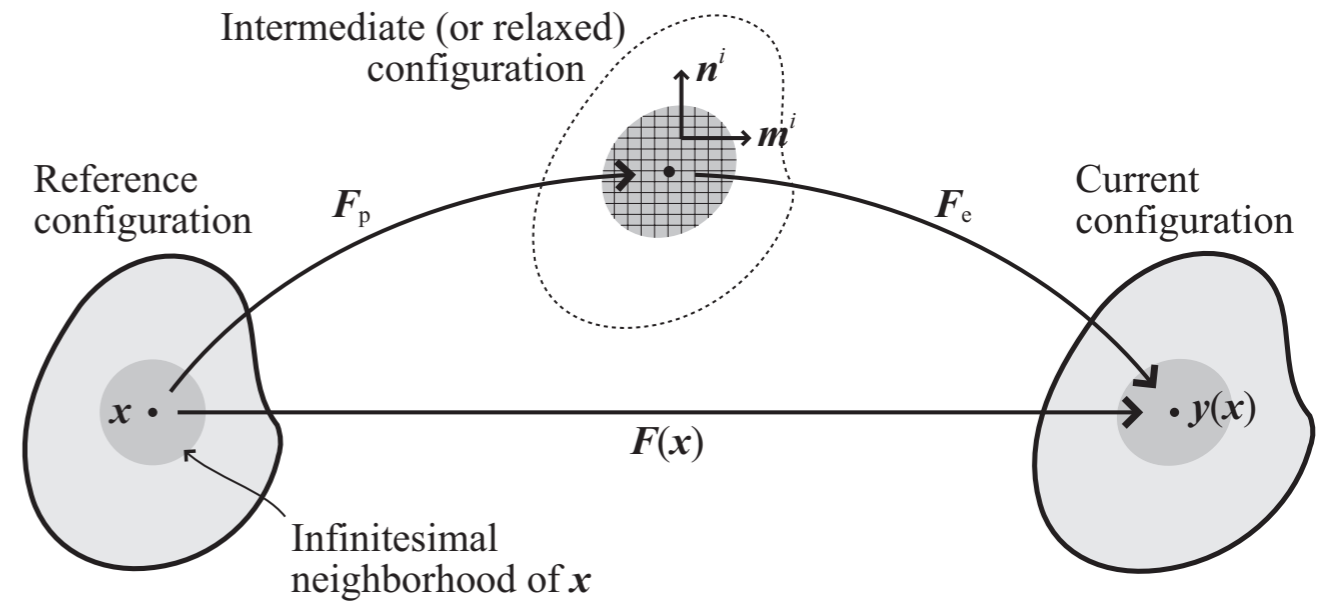


Recollection

Part I & II

recollection of part I & II

- deformation/velocity gradient characterizes *local* (at material point) change/rate of change of shape and size
- material point model connects stress (response) to strain (boundary cond.)
- finite strain plasticity introduces multiplicative decomposition with intermediate configuration
- solution of elastic/plastic strain partitioning requires \mathbf{L}^P from constitutive model



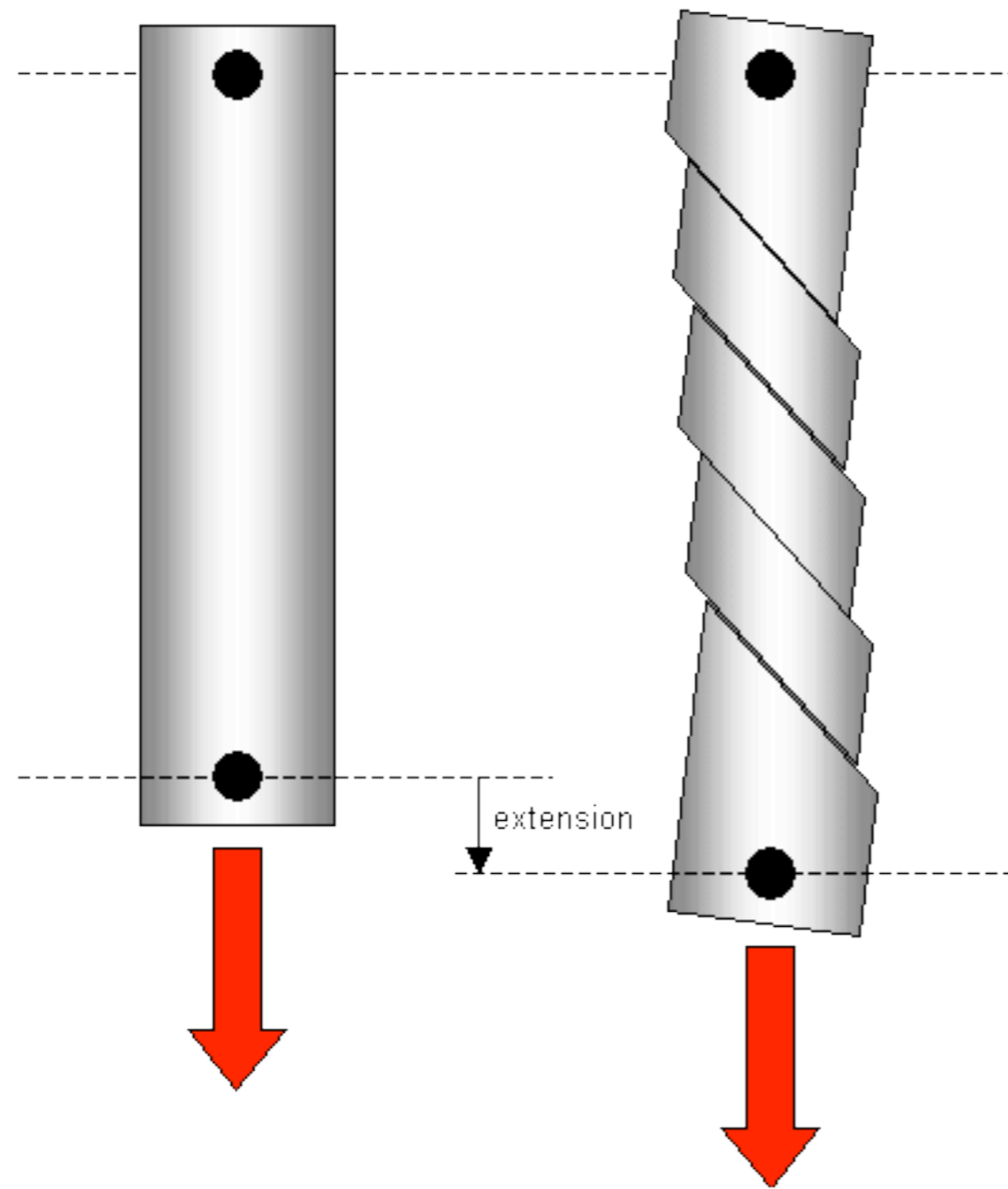
check out the source code...

crystallite.f90

PART III

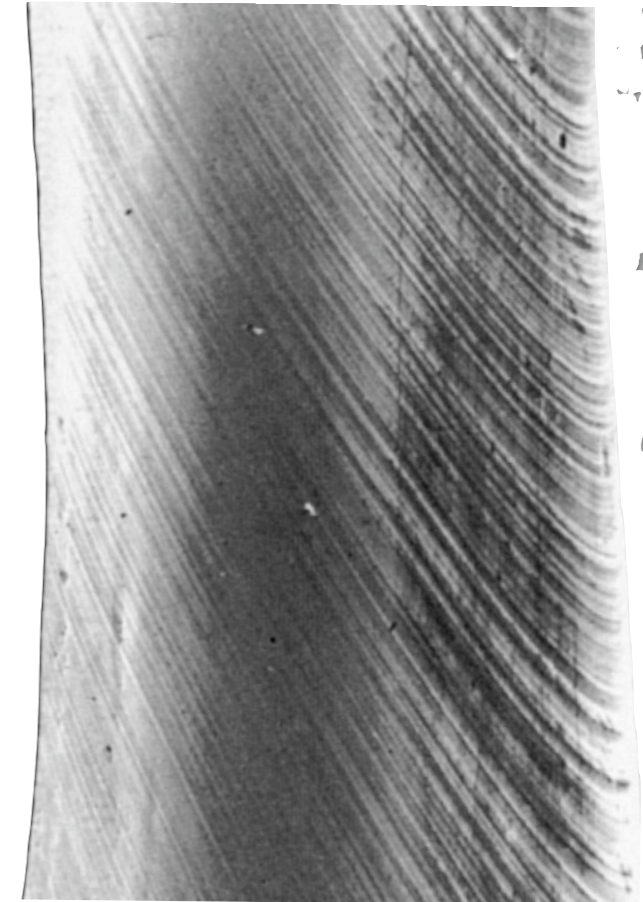
Monocrystal Plasticity Models

dislocation slip

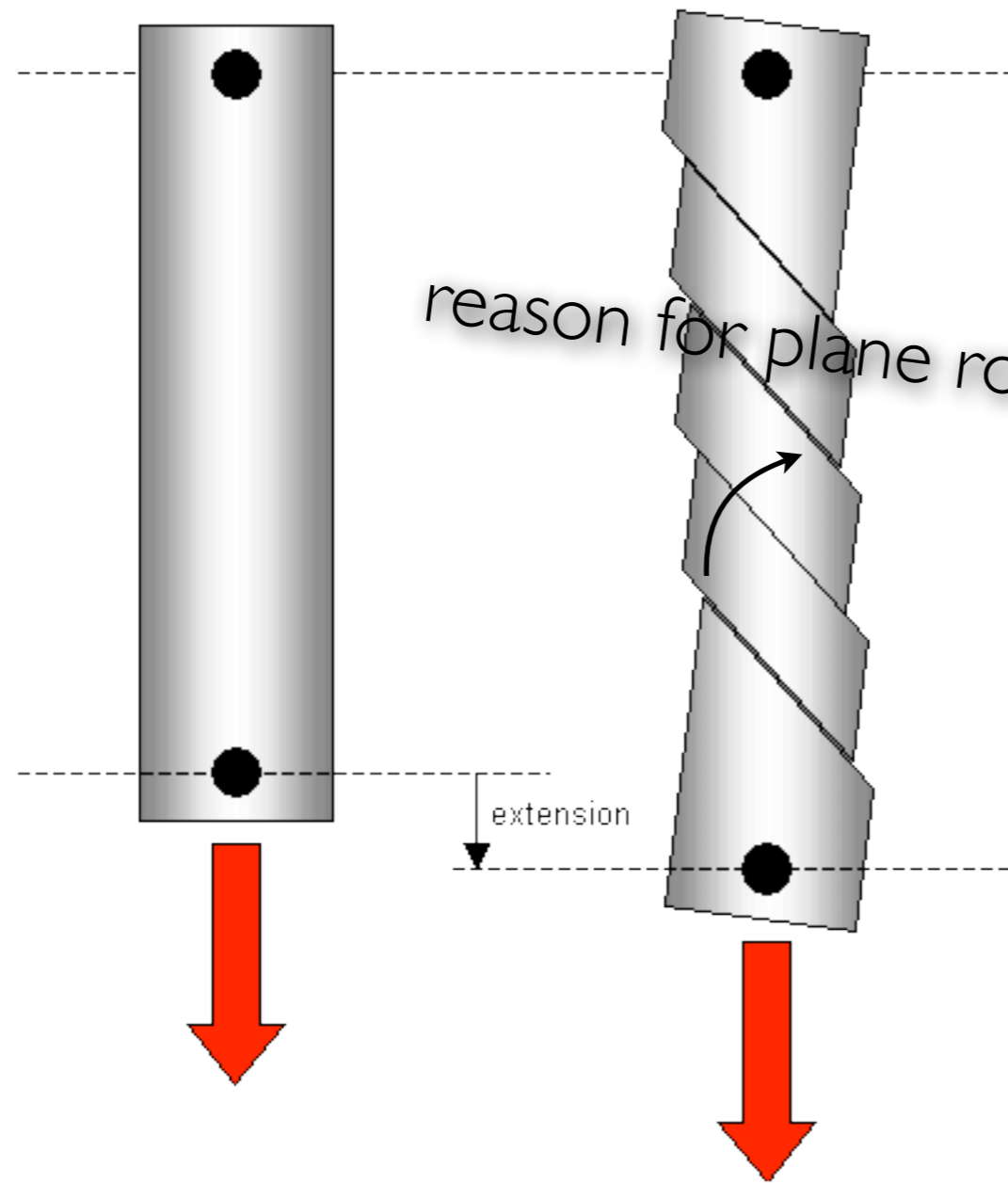


Unslipped single crystal fixed at top end.

Single crystal after plastic deformation by tensile stress in the direction of the arrow. Slip occurs on distinct parallel planes.

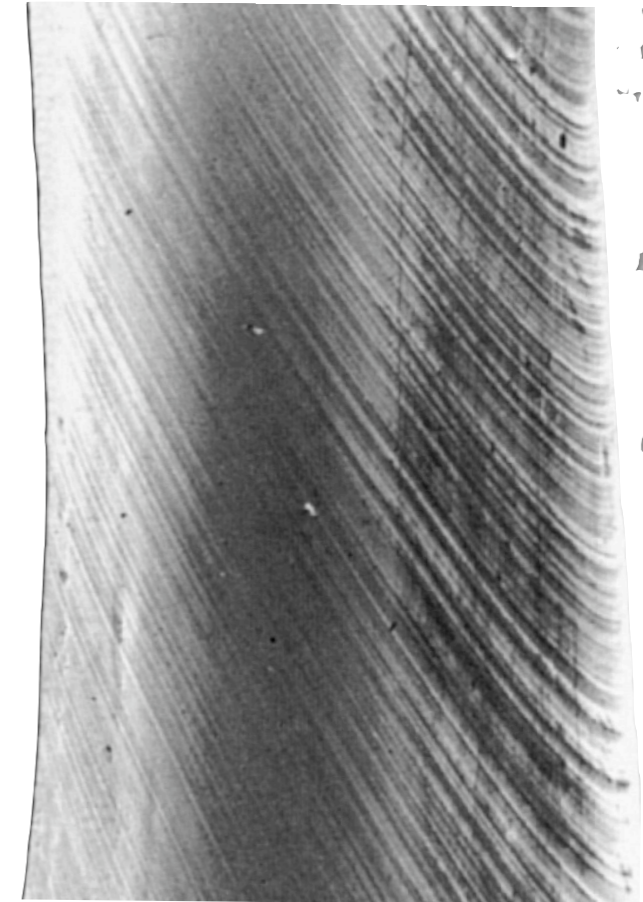


dislocation slip

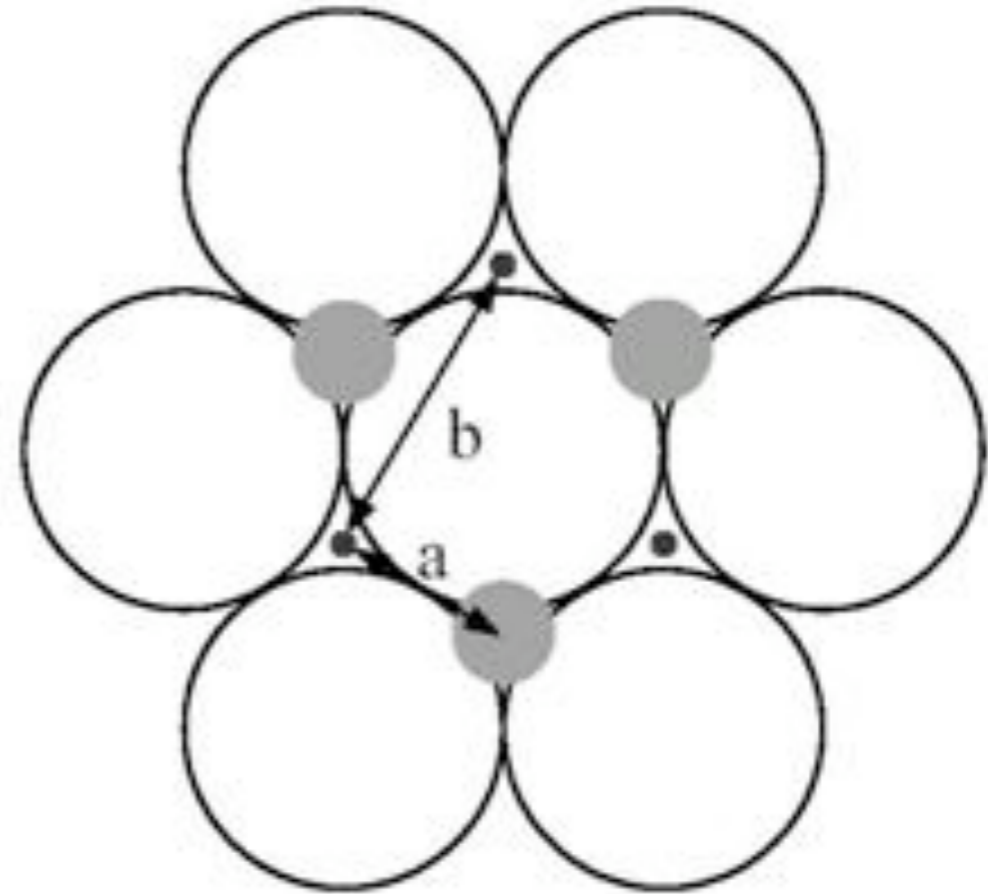
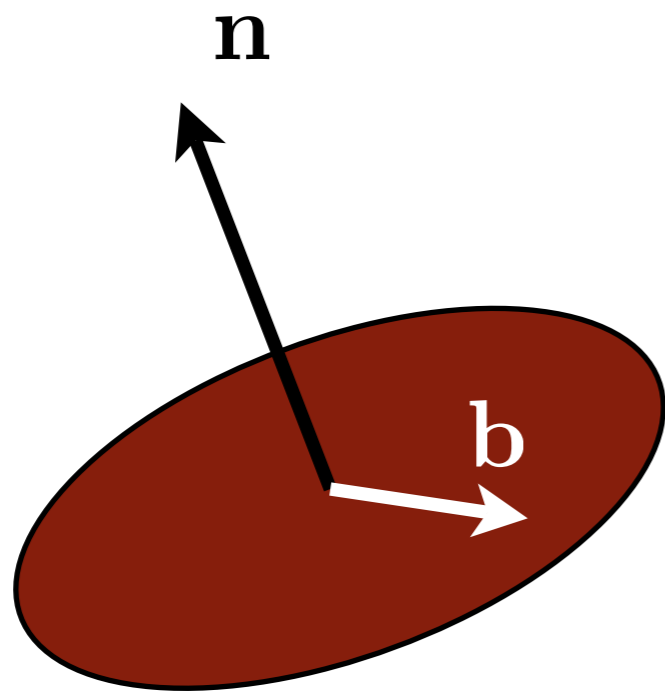


Unslipped single crystal fixed at top end.

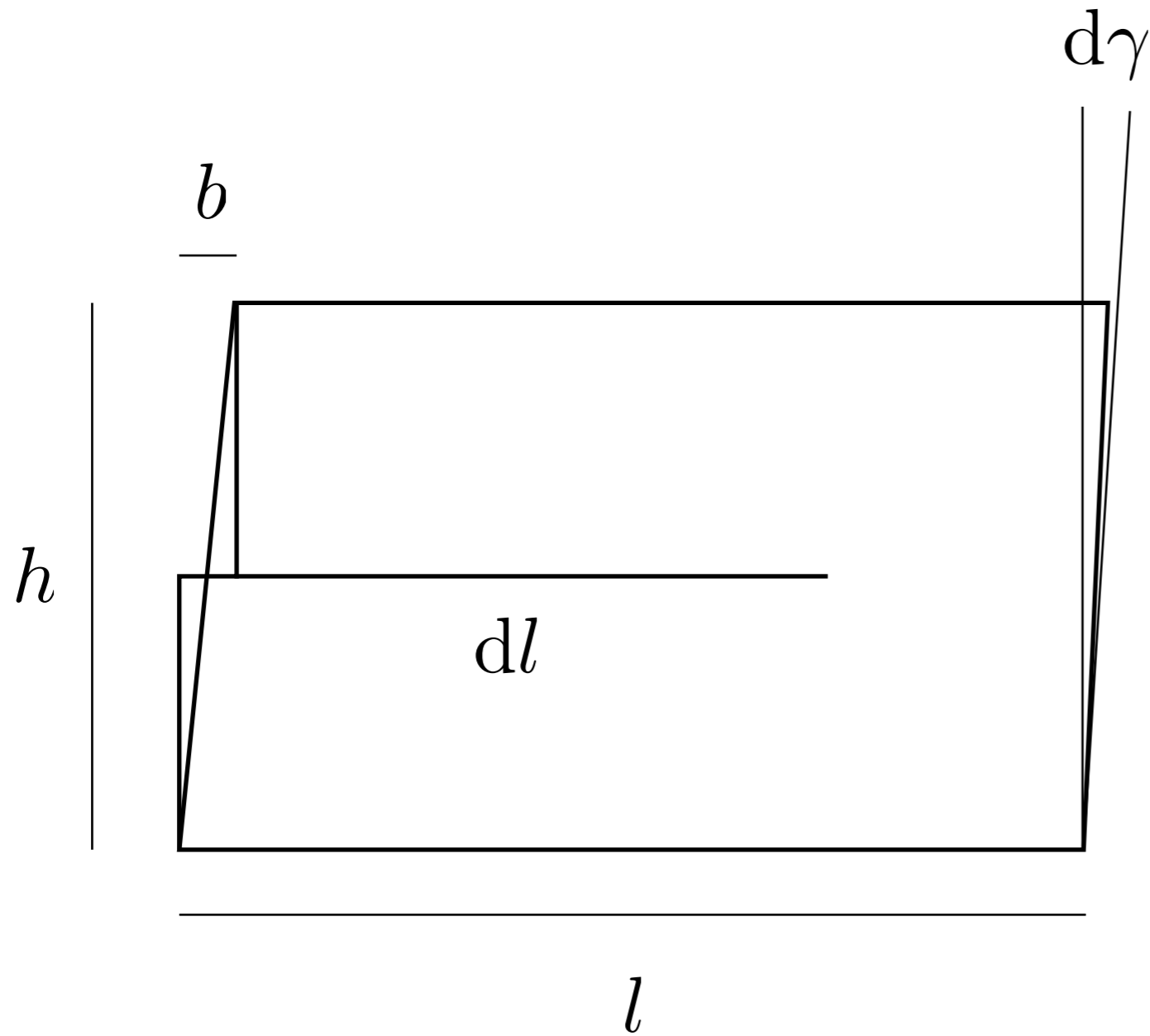
Single crystal after plastic deformation by tensile stress in the direction of the arrow. Slip occurs on distinct parallel planes.



slip systems in face centered cubic structure



shear from slip

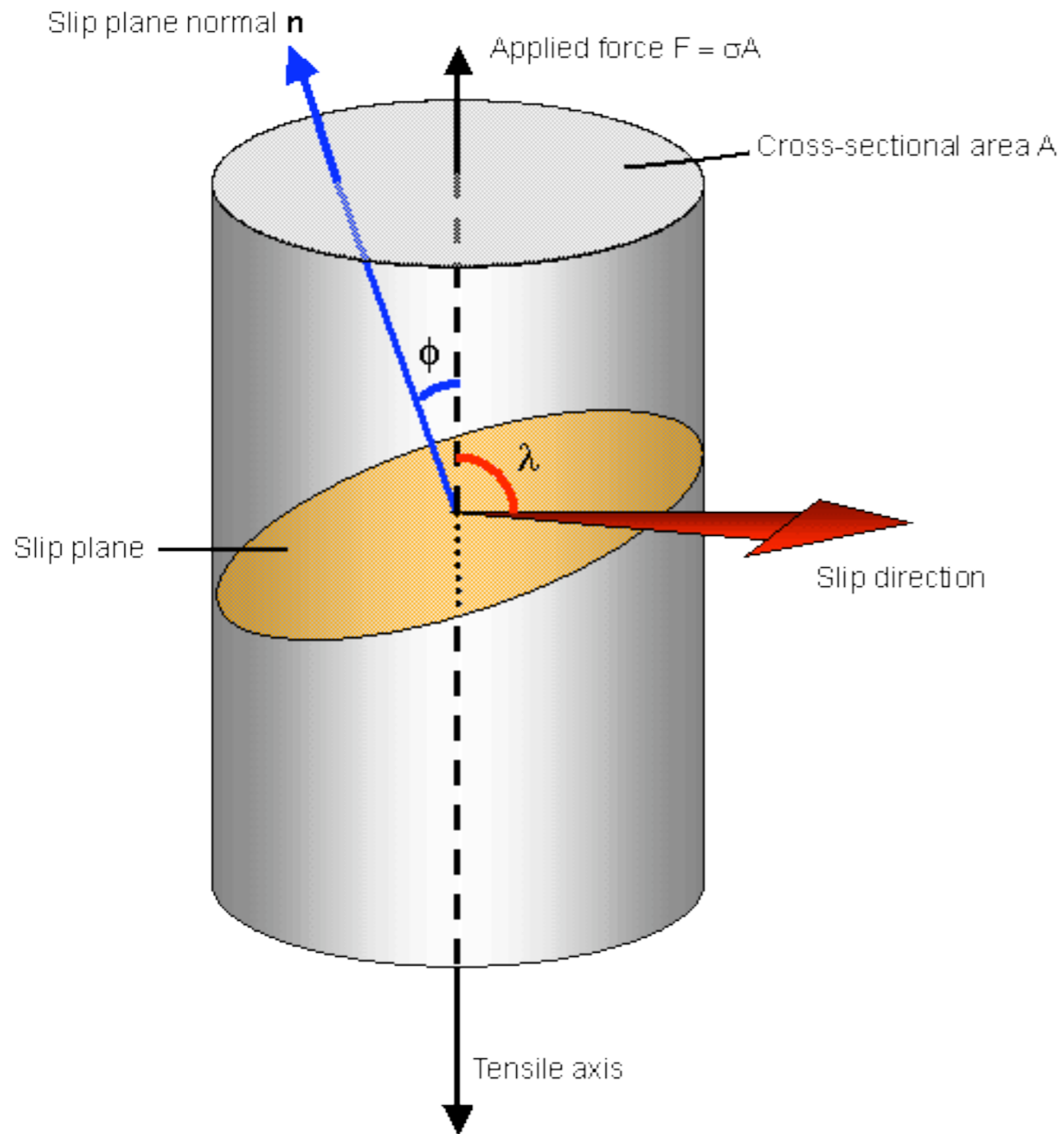


$$d\gamma = \frac{b \, dl}{h \, l}$$
$$= \frac{b \, dA}{V}$$

plastic velocity gradient

$$\begin{aligned}\mathbf{L}^p &= (\mathbf{L}^p)_{ij} \\ &= \frac{\partial \dot{x}_i}{\partial x_j} \\ &= \sum_{\alpha} \dot{\gamma}^{(\alpha)} \mathbf{b}^{(\alpha)} \otimes \mathbf{n}^{(\alpha)}\end{aligned}$$

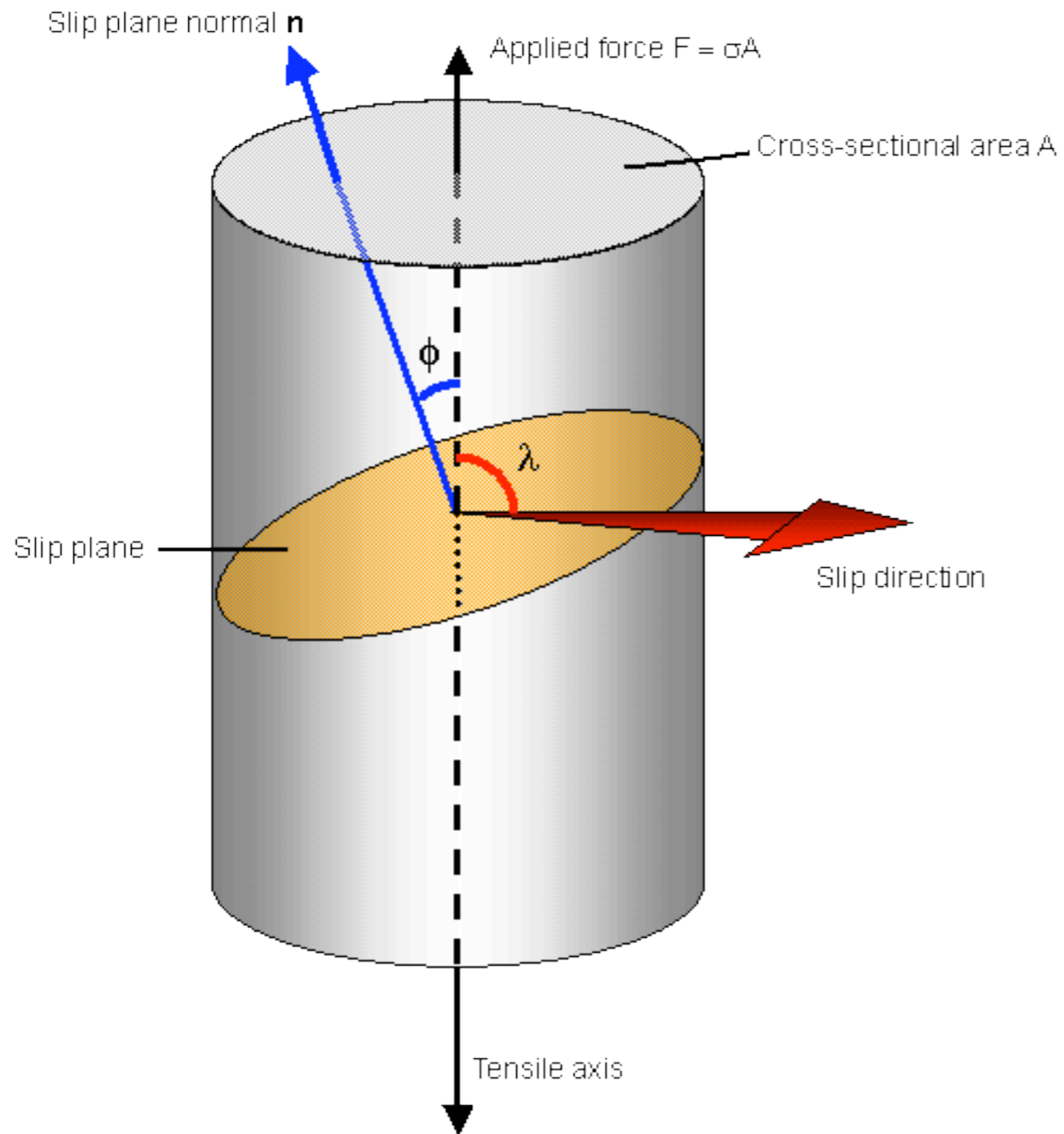
resolved shear stress



uniaxial

$$\tau^{(\alpha)} = \sigma \cos \phi^{(\alpha)} \cos \lambda^{(\alpha)}$$

resolved shear stress



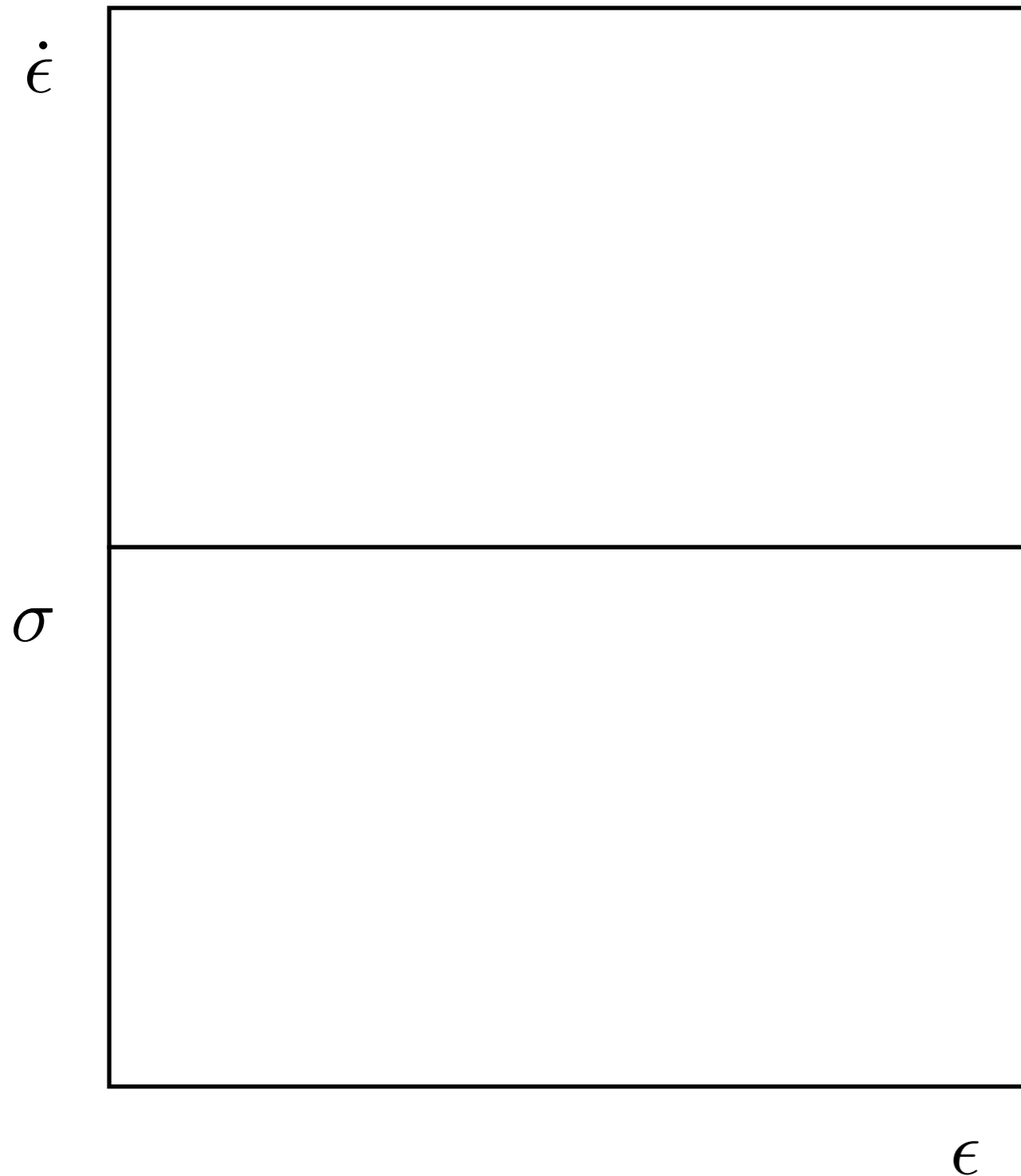
uniaxial

$$\tau^{(\alpha)} = \sigma \cos \phi^{(\alpha)} \cos \lambda^{(\alpha)}$$

general

$$\tau^{(\alpha)} = \mathbf{S} : (\mathbf{b}^{(\alpha)} \otimes \mathbf{n}^{(\alpha)})$$

room-temperature deformation resistance in fcc metals



- low strain-rate sensitivity
- largely monotonic decrease in strain hardening coefficient

phenomenological description

deformation kinetics

$$\dot{\gamma}^{(\alpha)} = \dot{\gamma}_0 \left| \frac{\tau^{(\alpha)}}{\tau_c^{(\alpha)}} \right|^n \text{sign } \tau^{(\alpha)}$$

microstructure evolution

$$\dot{\tau}_c^{(\alpha)} = \sum_{\beta} q_{\alpha\beta} h_0 \left(1 - \frac{\tau_c^{(\beta)}}{\tau_s} \right)^a \dot{\gamma}^{(\beta)}$$

drawbacks

- independent of temperature
- independent of strain path
- independent of grain size

basis

$$\begin{aligned}\dot{\gamma} &= \frac{b \dot{A}}{V} \\ &= b \frac{\ell}{V} \dot{w} \\ &= b \rho_m v\end{aligned}$$

issues

- parameterization of microstructure
- velocity of dislocations
- evolution of microstructure

density on each system

$$\rho^{(\alpha)} \quad \text{with } \alpha = 1, \dots, 12$$

projected perpendicular density

$$\rho_{\perp}^{(\alpha)} = \frac{1}{2} \sum_{\beta} \rho^{(\beta)} \left[|\mathbf{n}^{(\alpha)} \cdot (\mathbf{n}^{(\beta)} \times \mathbf{b}^{(\beta)})| + |\mathbf{n}^{(\alpha)} \cdot \mathbf{b}^{(\beta)}| \right]$$

projected parallel density

$$\rho_{\parallel}^{(\alpha)} = \frac{1}{2} \sum_{\beta} \rho^{(\beta)} \left[\|\mathbf{n}^{(\alpha)} \times (\mathbf{n}^{(\beta)} \times \mathbf{b}^{(\beta)})\| + \|\mathbf{n}^{(\alpha)} \times \mathbf{b}^{(\beta)}\| \right]$$

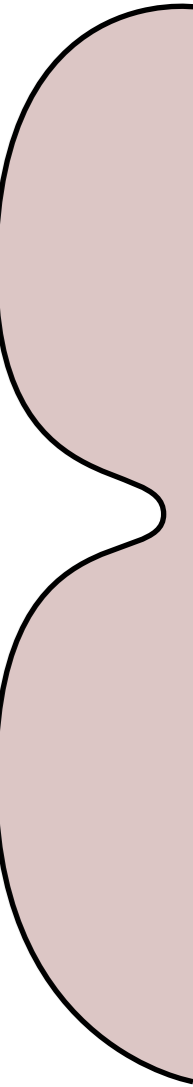
derived mobile density

$$\frac{\partial \tau^{(\alpha)}}{\partial \rho_m^{(\alpha)}} = 0$$
$$\Rightarrow \rho_m^{(\alpha)} \propto \sqrt{\rho_{\parallel}^{(\alpha)} \rho_{\perp}^{(\alpha)}}$$

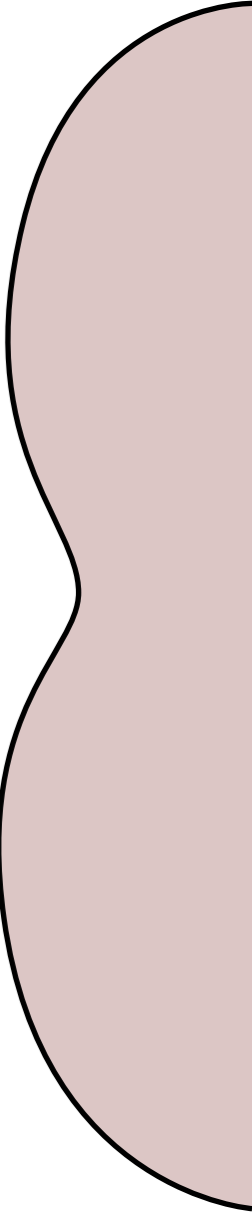
(specific) dipole density



(specific) dipole density



(specific) dipole density



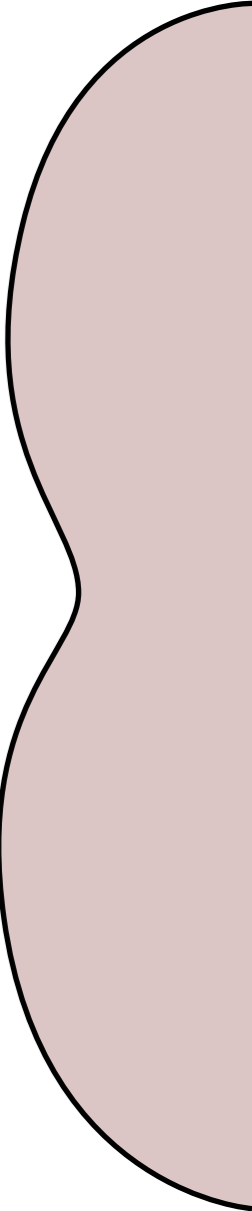
(specific) dipole density

$$\varrho_{\text{sgl}}^{(\alpha)} \quad \text{with } \alpha = 1, \dots, 12$$

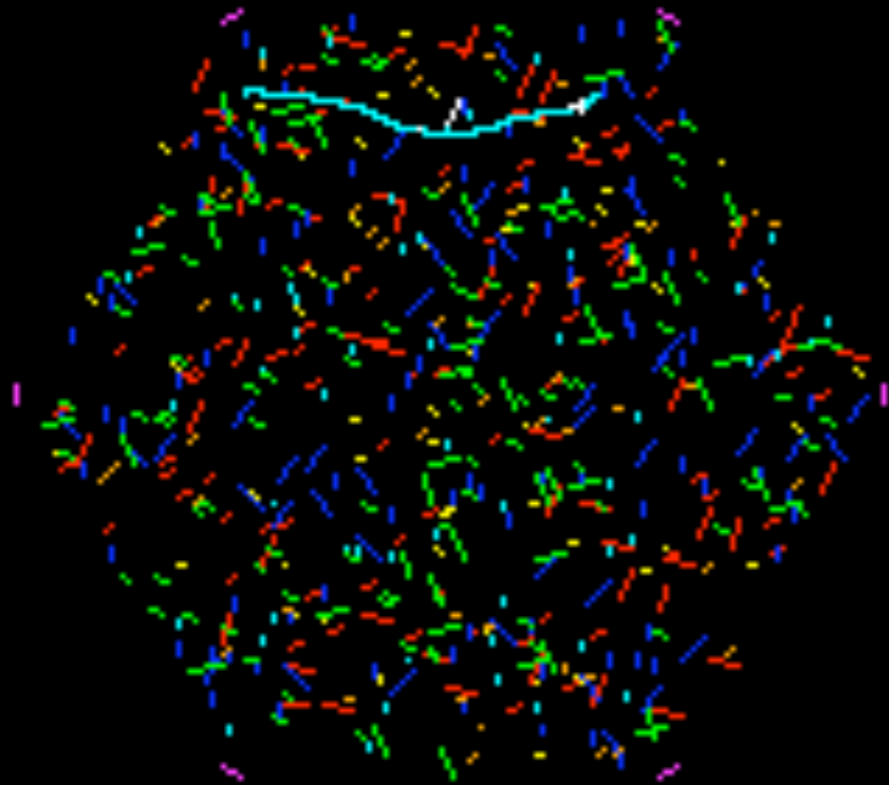
$$\varrho_{\text{dip}}^{(\alpha)} \quad \text{with } \alpha = 1, \dots, 12$$

$$\chi^{(\alpha)} \equiv \frac{\partial \varrho_{\text{dip}}^{(\alpha)}}{\partial h} \quad \text{with } \alpha = 1, \dots, 12$$

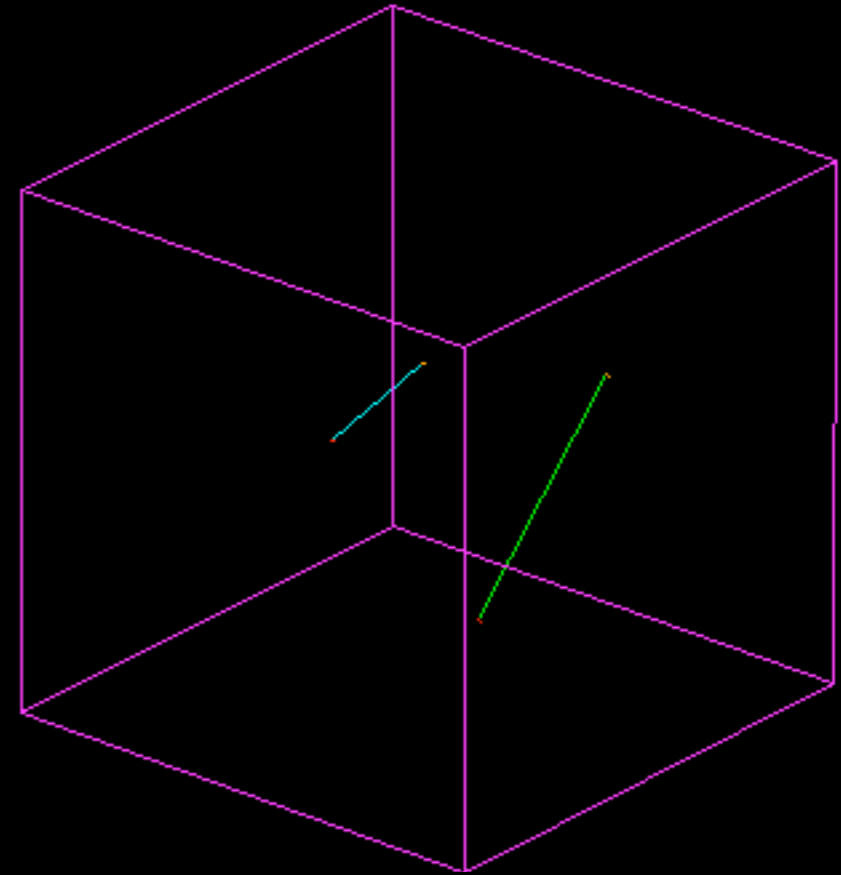
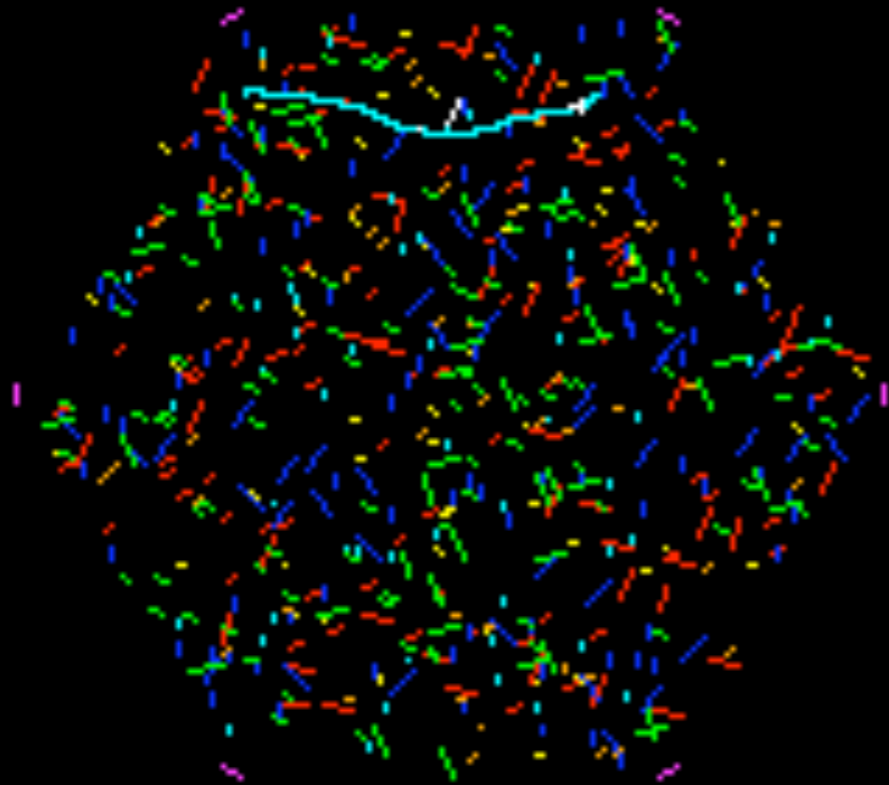
$$h_{\text{spon}} < h < \hat{h}^{(\alpha)} \equiv \frac{1}{8\pi(1-\nu)} \frac{Gb}{\tau^{(\alpha)}}$$



dislocation–forest interaction

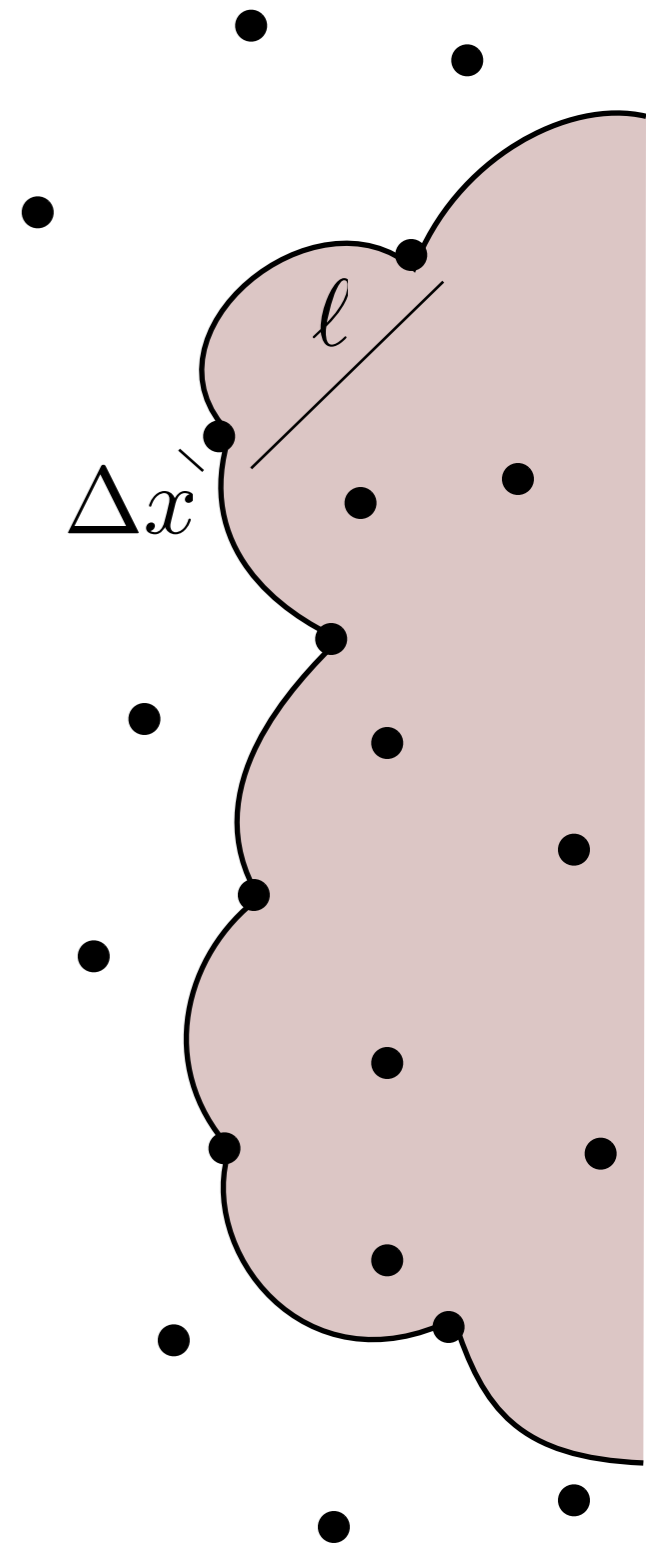


dislocation–forest interaction



thermally activated forest cutting

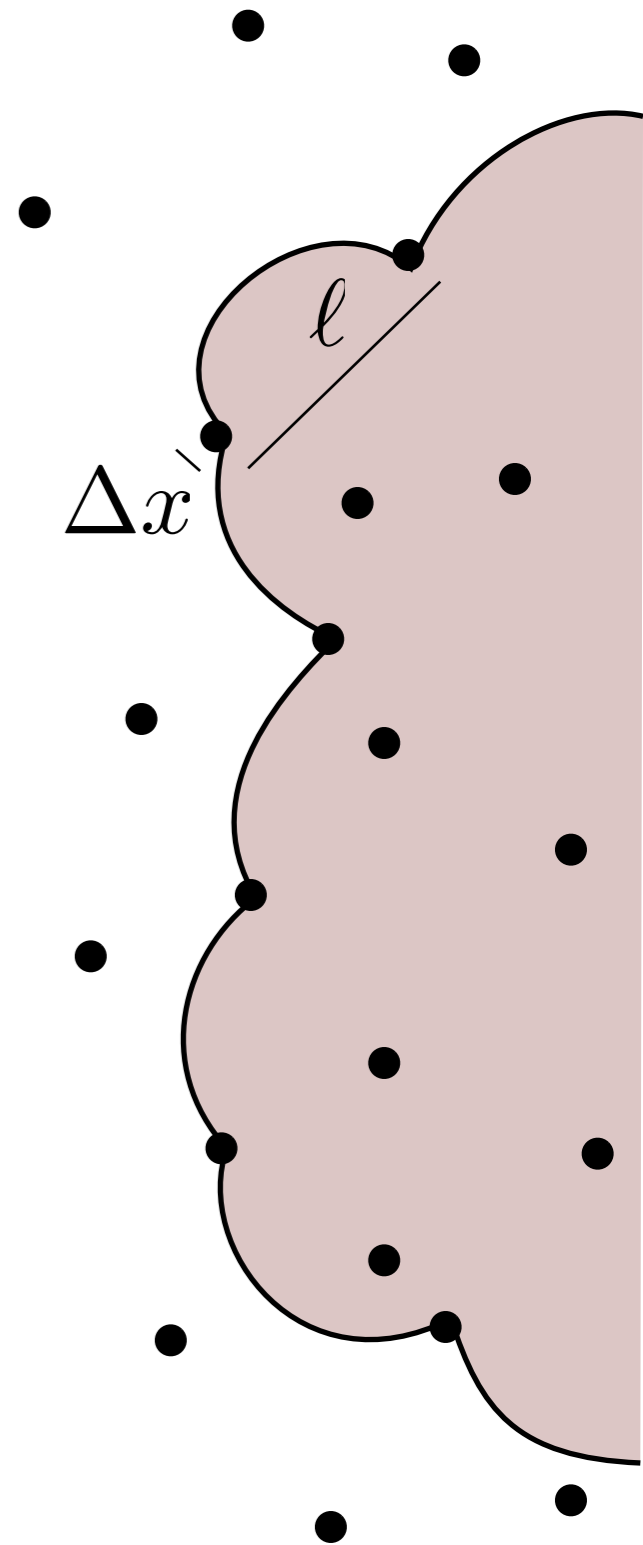
$$v^{(\alpha)} = \lambda^{(\alpha)} \nu_{\text{attack}} \text{sign} \left(\tau^{(\alpha)} \right) \times \exp \left(-\frac{Q_{\text{slip}}}{k_{\text{B}} T} \right) \sinh \left(\frac{\tau_{\text{eff}}^{(\alpha)} V^{(\alpha)}}{k_{\text{B}} T} \right)$$



thermally activated forest cutting

$$v^{(\alpha)} = \lambda^{(\alpha)} \nu_{\text{attack}} \text{sign} \left(\tau^{(\alpha)} \right) \times$$
$$\exp \left(-\frac{Q_{\text{slip}}}{k_{\text{B}} T} \right) \sinh \left(\frac{\tau_{\text{eff}}^{(\alpha)} V^{(\alpha)}}{k_{\text{B}} T} \right)$$

$V^{(\alpha)} = b \ell \Delta x$

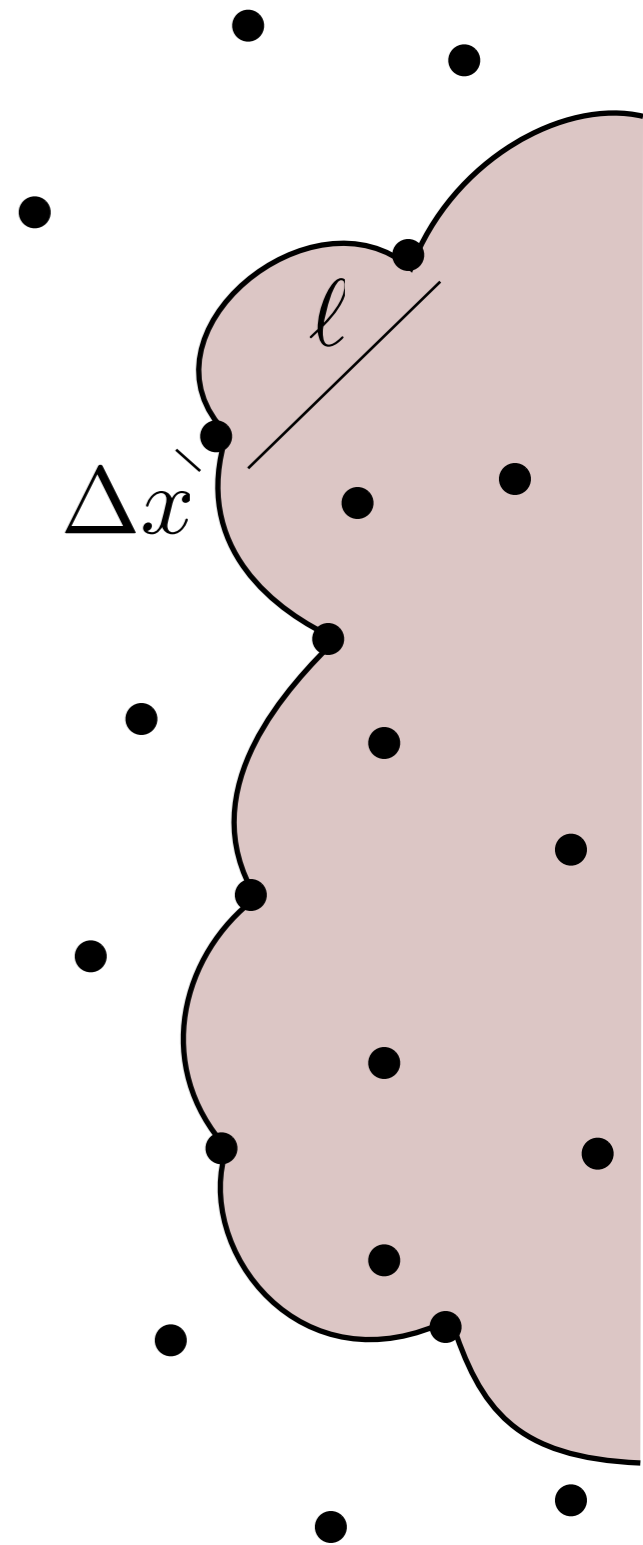


thermally activated forest cutting

$$v^{(\alpha)} = \lambda^{(\alpha)} \nu_{\text{attack}} \text{sign} \left(\tau^{(\alpha)} \right) \times \exp \left(-\frac{Q_{\text{slip}}}{k_{\text{B}} T} \right) \sinh \left(\frac{\tau_{\text{eff}}^{(\alpha)} V^{(\alpha)}}{k_{\text{B}} T} \right)$$

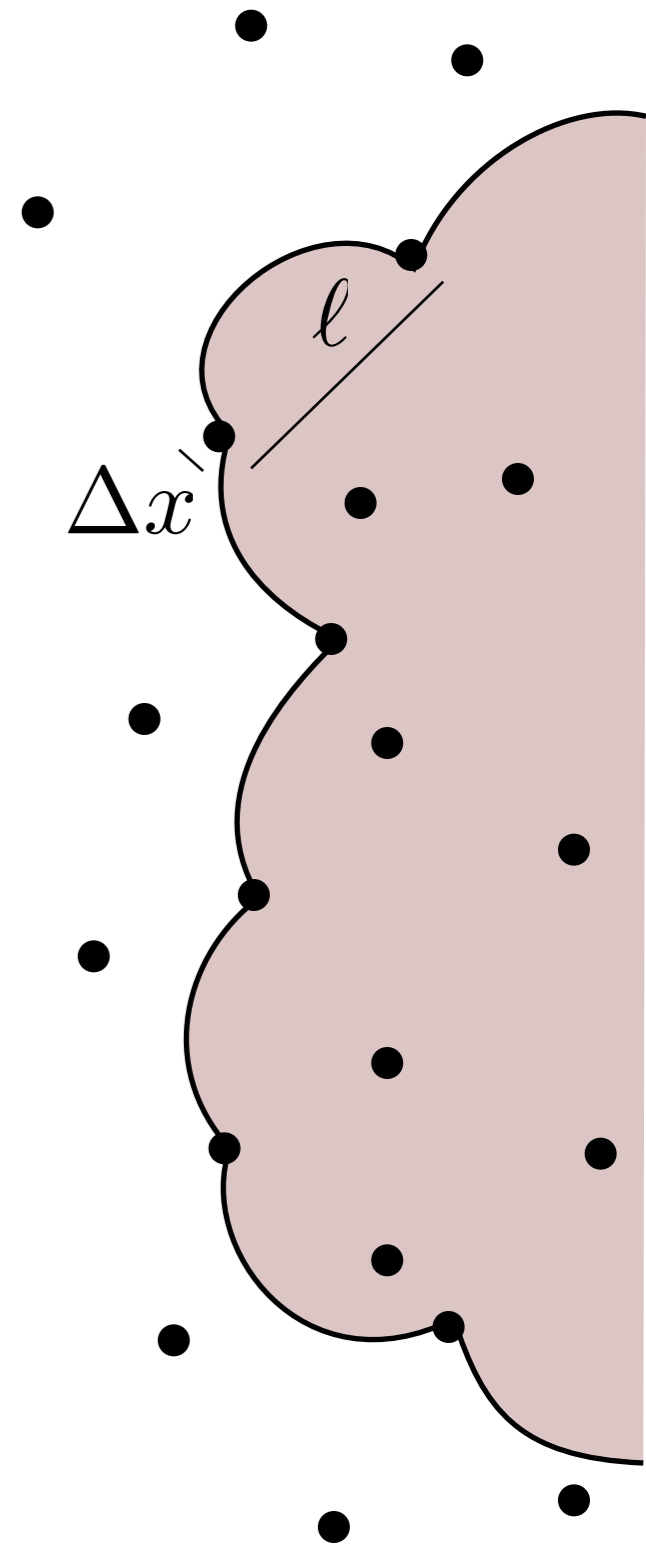
$$V^{(\alpha)} = b \ell \Delta x$$

$$\ell \propto \left(\rho_{\perp}^{(\alpha)} \right)^{-0.5}$$



thermally activated forest cutting

$$v^{(\alpha)} = \lambda^{(\alpha)} \nu_{\text{attack}} \text{sign} \left(\tau^{(\alpha)} \right) \times \exp \left(-\frac{Q_{\text{slip}}}{k_{\text{B}} T} \right) \sinh \left(\frac{\tau_{\text{eff}}^{(\alpha)} V^{(\alpha)}}{k_{\text{B}} T} \right)$$



thermally activated forest cutting

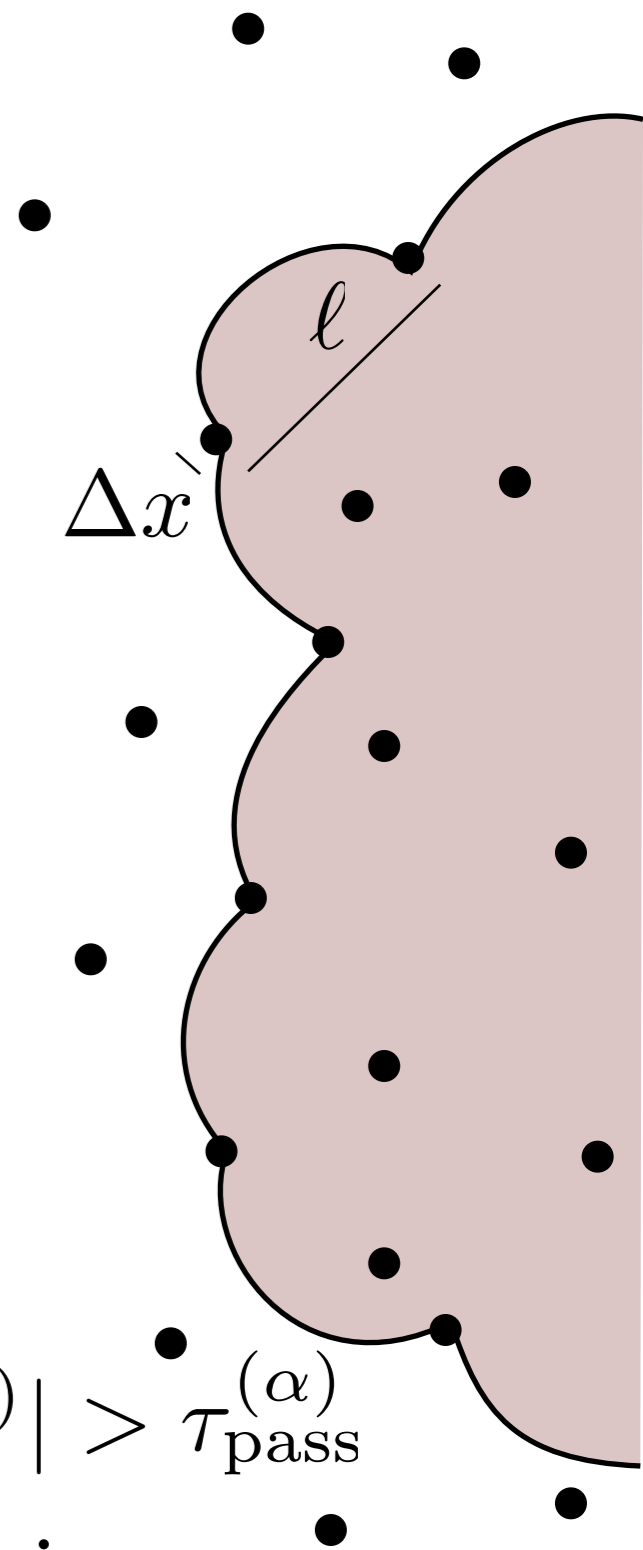
$$v^{(\alpha)} = \lambda^{(\alpha)} \nu_{\text{attack}} \text{sign} \left(\tau^{(\alpha)} \right) \times \exp \left(-\frac{Q_{\text{slip}}}{k_{\text{B}} T} \right) \sinh \left(\frac{\tau_{\text{eff}}^{(\alpha)} V^{(\alpha)}}{k_{\text{B}} T} \right)$$

$$\tau_{\text{eff}}^{(\alpha)} = |\tau^{(\alpha)}| - \tau_{\text{pass}}^{(\alpha)}$$

$$= \begin{cases} |\tau^{(\alpha)}| - c_3 G b \sqrt{\rho_{\parallel}^{(\alpha)} + \rho_{\text{m}}^{(\alpha)}} \\ 0 \end{cases}$$

if $|\tau^{(\alpha)}| > \tau_{\text{pass}}^{(\alpha)}$

otherwise



dislocation structure evolution

$$\dot{\chi} = \frac{2\dot{\gamma}}{bN_g} \left[\underbrace{\underbrace{Q_{\text{sgl}}}_{\text{dipole formation}}}_{\text{dipole formation}} + \underbrace{\int_h^{\hat{h}} \chi dh' - \chi h}_{\text{exchange of constituents}} - \underbrace{\chi h \left(\frac{1}{1 - 0.9h/\hat{h}} - 1 \right)}_{\text{dipole decomposition}} \right] + \underbrace{\frac{2v_c \chi}{h} \left(\frac{\partial(\ln \chi)}{\partial(\ln h)} - 1 \right)}_{\text{climb of constituents}}$$

$$\dot{Q}_{\text{sgl}} = \frac{2\dot{\gamma}}{bN_g} \left(\underbrace{\frac{N_g}{2\Lambda}}_{\text{dislocation generation}} - \underbrace{\hat{h} Q_{\text{sgl}}}_{\text{dipole formation}} + \underbrace{\int_{h_{\text{spon}}}^{\hat{h}} \chi h \left(\frac{1}{1 - 0.9h/\hat{h}} - 1 \right) dh}_{\text{dipole decomposition}} \right)$$

check out the source code...

constitutive.f90